

MMBT589L

30 V, 1.0 A High Current PNP Low $V_{CE(sat)}$ Bipolar Transistor

Product Overview

For complete documentation, see the data sheet.

Low $V_{CE(sat)}$ Bipolar Transistors are miniature surface mount devices featuring ultra low saturation voltage $V_{CE(sat)}$ and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Features

- Low $r_{DS(on)}$ Provides Higher Efficiency and Extends Battery Life
- Miniature SOT-23 Surface Mount Package Saves Board Space
- Pb-Free Packages are Available
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AECQ101 Qualified and PPAP Capable

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Polarity	Type	$V_{CE(sat) Max}$ (V)	I_C Cont. (A)	$V_{CE0 Min}$ (V)	V_{CBO} (V)	V_{EBO} (V)	$V_{BE(sat)}$ (V)	$V_{BE(o)}$ (V)	$h_{FE Min}$	$h_{FE Max}$	f_T Min (MHz)	$P_{TM Max}$ (W)	Package Type
MMBT589LT1G	0.096		Active	PNP	General Purpose	0.3	1	30	50	5	1.2	1.1	100	300	100	0.31	SOT-23-3
NSVMMBT589LT1G	0.176		Active	PNP	General Purpose	0.3	1	30	50	5	1.2	1.1	100	300	100	0.31	SOT-23-3